E ect of oxygen content on the transport properties and m agnetoresistance in $[C a_2 C OO_3]_{0.62} [C OO_2]$ single crystals

X.G.Luo, X.H.Chen, G.Y.W ang, C.H.W ang, Y.M.Xiong, H.B.Song, H.Liand X.X.Lu

Hefei National Laboratory for Physical Science at Microscale and Department of Physics,

University of Science and Technology of China, Hefei, Anhui 230026, People's Republic of China

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Transport property is investigated in $[Ca_2CoO_3]_{b:62}$ $[CoO_2]$ single crystals obtained by varying annealing conditions. The $_{ab}(T)$ exhibits a resistivity m inim um , and the tem perature corresponding to this m inim um increases with the loss of oxygen content, indicative of the enhancem ent of spin density wave (SDW). Large negative m agnetoresistance (MR) was observed in all single crystals $[Ca_2CoO_3]_{b:62}$ $[CoO_2]$, while a m agnetic-eld-driven insulator-to-m etal (IM) transition in oxygen annealed sam ples. These results suggest a ferrom agnetic correlation in system enhanced by oxygen content. In addition, a low tem perature therm all activation resistivity induced by elds was observed in single crystals annealed in oxygen atm osphere.

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I. IN TRODUCTION

M is t-layered cobalt oxides attracted a great deal of interest for their possession of unusual electrical properties such as large negative magnetoresistance, 1,2,3,4 coherent-incoherent transition with varying tem- $(B_{1}P_{b})_{2}B_{3}C_{2}O_{9}^{5}$ and perature in а large thermoelectric power (TP) with metallic resistivity observed in $(Bi_Pb)_2 Sr_2 Co_2 O_9$, ^{5,6} $Ca_3 Co_4 O_9$ $([Ca_2CoO_3]_{0:62} [CoO_2])^1$ and $Tb_{:4} (Sr_{0:9}O)_{1:12}CoO_2^7$ Besides the e ort to enhance the therm oelectric gure of merit $ZT = S^2T /$ for the application reason, as a transition metal oxide with strong correlation and anom alous electronic structure, many studies were focused on their physical nature. Recently, another prom ising therm oelectric triangular cobaltite Na_xCoO_2 , was found to exhibit superconductivity below 5 K by intercalating water molecules into between the Na⁺ and $C \circ O_2$ layers in the composition of x= 0.35.⁸ Later, Foo et al,⁹ observed an insulating resistivity below 50 K in the com position of x = 0.5, which is related to the strong coupling of the holes and the long-range ordered Na^+ ions. The strong dependence of therm opower on magnetic

eld in NaCOO₂ provides a unambiguous evidence of strong electron-electron correlation in the therm oelectric cobalt oxides.¹⁰ The large TP with metallic resistivity, superconductivity, charge ordering existing in various x, displays a complicated and profise electronic state in Na_xCOO₂. This has inspired num erous theoretical and experimental studies on the therm oelectric cobaltite.

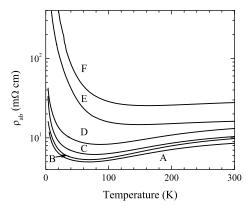
In this paper we focus on one of the therm oelectric cobalt oxides, $[Ca_2COO_3 \ b_{162} [COO_2]$ system. Because of the large ZT (1 at 1000 K),¹¹ $Ca_3Co_4O_9$ is thought to be one of the most promising candidate for a p-type material component of therm oelectric power generation systems. $[Ca_2COO_3 \ b_{162} [COO_2]$ has a complex magnetic structure, including the spin-state transition of cobalt ions from low -spin to interm ediate-spin+high-spin or high-spin at about 380 K, the spin density wave transition with onset temperature $T_{SDW}^{on} = 100$ K and tran-

sition width T = 70 K, and the ferrin agnetism below 19 K .^{1,12} Transport properties are closely related to the magnetism due to the coupling between the charge and spin degree of freedom. The spin state transition of cobalt ions around 380 K leads to an abrupt jum p of resistivity with decreasing tem perature; $t^{1,12}$ the emergence of insulator-like behavior below about 70 K was thought to be related to the appearance of short-range SDW order. 12 $[Ca_2CoO_3]_{0:62}$ $[CoO_2]$ also has a complex crystal structure. The crystal structure of $[Ca_2CoO_3]_{0:62}[CoO_2]$ consists of alternating stacks of two monoclinic subsystem s along the c-axis: the triple Ca_2CoO_{3+} rocksalttype layers and single CdI2-type CoO2 triangular sheet (conducting layers).¹ The m is t between the two subsystems leads to an incommensurate (IC) spatial modulation along b axis. The $[Ca_2CoO_3]_{0:62}[CoO_2]$ system could exhibit very complicated electronic transport properties due to the com plex m agnetic and crystal structure. Strong m agnetic eld is a very useful tool to investigate the correlation between charge dynam ics and m agnetism. The interesting phenom enon could be expected under high magnetic eld due to the strong coupling between the charge and spin degrees of freedom. Large negative MR has been reported in previous work, 1 but only on curve of (T) vs. T under the magnetic eld of 7 T was presented. Detailed investigation is lacking to make out the mechanism for the MR yet. In this paper, the ab (T) is studied with varying annealing condition. It is found that the ab (T) exhibits a minimum. The tem perature corresponding to this minimum (T_{min}) increases with the loss of oxygen content, indicative of the enhancement of SDW. The magnetoresistance were also m easured up to 14 T in the $[Ca_2CoO_3]_{0:62}$ [CoO₂] single crystals. Large negative M R was observed in all sam ples. An insulator-to-m etal (\mathbb{M}) transition were observed for oxygen annealed crystals in high magnetic elds. The magnetic- eld-driven charge dynamics is attributed to the enhancem ent of ferrom agnetic correlation.

II. EXPERIMENTAL

The single crystals used in the measurements were grown by the solution method as described in ref.(13) using K_2CO_3 -KClas uxes with composition of 4:1. The typical dimension of the crystals are 5 5 0.02 mm³. In order to study the oxygen content (or carrier concentration) e ect on the charge transport, as-grown crystals were annealed in owing oxygen atm osphere at 723 K for 12 h, 11 h, 10 h and 8 h, , which were denoted as crystalA, B, C and D, respectively. The as-grown crystal is denoted as crystalE.Som e other crystals were annealed owing nitrogen atmosphere at 723 K for 10 h, dein noted as crystal F.W e found that the charge transport is sensitive to the annealing time (oxygen content). The details will be discussed in the following section. This result is consistent with the reported by K arppinen et al.¹⁴ Resistance measurements were performed using the ac four-probe method with an ac resistance bridge system (Linear Research, Inc.; LR-700P). The dcm agnetic eld for m agnetoresistance m easurem ents is supplied by a superconducting magnet system (Oxford Instruments). In the text following, we abbreviate $[Ca_2CoO_3]_{0:62}$ $[CoO_2]$ to $Ca_3Co_4O_9$ for simplicity.

III. EXPERIMENTAL RESULTS



A. Transport properties

FIG. 1: The temperature dependence of resistivity for the $Ca_3Co_4O_9$ crystals annealed in various conditions. The curve A, B, C, D correspond to the resistivity of the crystal annealed in oxygen ow at 723 K for 12 h, 11h, 10h, 8h, respectively. The curve E and F are obtained from as-grown crystal and nitrogen-annealed crystal, respectively.

Figure 1 shows the (T) curves of the C a_3 C o_4 O $_9$ single crystals annealed in various conditions. There are some common features in (T) among the crystals. The

(T) is m etallic in high tem peratures and shows a broad m inim um with decreasing tem perature. Below the tem – perature of resistivity m inim um ($T_{m \ in}$), the (T) exhibits a diverging behavior. The crystalA, which was annealed in oxygen ow at 723 K for 12 h has the lowest resis-

tivity (the curve A) and $T_{m in}$ (68.8 K) among the listed samples. The ratio (T = 4 K)/(T = 300 K) is also the sm allest. This indicates that this sample corresponds to the highest hole concentration. W ith decreasing the annealing time in oxygen ow at 723 K, $T_{m in}$ and the ratio

(T = 4 K)/ (T = 300 K) increases, indicative of the decrease of the hole concentration. This dem onstrates that annealing in oxygen atmosphere enhances the oxygen content in the crystals. The hole concentration increases with the enhancement of oxygen content. The crystal annealed in nitrogen ow exhibits the largest resistivity among all samples, and it also possesses the largest $T_{m in}$ (169 K), indicating that this crystal have the low est hole concentrations and oxygen content. The asgrow n crystalhas the resistivity and $T_{m in}$ between that of the oxygen-annealed crystals and nitrogen-annealed one, manifesting a hole concentration between them. Thus the annealing in nitrogen ow is a procedure of reducing oxygen content, while in oxygen ow enhancing oxygen content. This is consistent with the results reported by Karppinen et al.¹⁴ They found that the oxygen content is easily changed just by ambient pressure in low oxygen content regime. The di erence in $C_{q_{0}}C_{0_{1}}$ is as high as 0.24 between N $_{\rm 2}$ annealed sample and sam ple prepared in air. However, the annealing has to be perform ed at high oxygen pressure to change the oxygen content in the large regime. The di erence between our and their works is that their work was carried out on the polycrystalline samples, while the data presented here on single crystals. Fig. 1 clearly shows that the charge transport is sensitive to the oxygen content in the crystals, which increases with enhancing annealing time at 723 K in oxygen ow. In addition, it can be found that T_{m in} decreases with increasing the oxygen content from 149 K in the curve E to 68.8 K in the curve A. Sugiyam a et al. suggested that the resistivity m inim um is associated with the SDW transition. A coording to this point of view, the SDW can be enhanced by decreasing the oxygen content, equivalently, reducing the Co ions valence. This is consistent with the e ect of Bi and Y doping in the $Ca_3Co_4O_9$, where the T_{SDW}^{on} is enhanced by 30 K at the doping level of 0.3 with decreasing the Covalence. These results indicate that the SDW is very sensitive to the Co ions valence. It should be pointed out that annealing in nitrogen m ay have a much stronger e ect on the enhancement of SDW than the Y and Bi doping because the $T_{\text{m in}}$ of the curve F is enhanced by about 100 K relative to that of curve A, though the exact transition tem perature of SDW cannot be determ ined.

B. M agnetotransport phenom ena

1. Magnetoresistance

Figure 2 (a) shows the in-plane resistivity of the crystal A as the function of temperature in the range of 4 K to 70 K in various magnetic elds up to 14 T. This crystal was annealed in oxygen ow at 723 K for 12 h. The

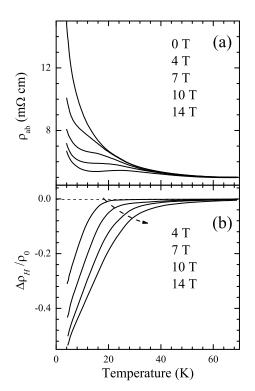


FIG.2: (a)The temperature dependence of the resistivity for the crystal A at di erent elds. (b) The temperature dependence of $_{\rm H} = _0 = [$ (H) (0)]/ (0) at di erent elds. The dashed arrow in the (b) guides one's eyes for the temperature below which the negative M R begins to increase rapidly.

eld is applied along the c-axis. At zero eld the sam ple is metallic (d $_{ab}/dT > 0$) in high temperatures, and exhibits a minimum of (T) at 68.8 K. Below 68.8 K the crystal shows an insulator-like behavior. The (T) in whole range of T at zero eld has been shown by the curve A of g. 1. The value of ab (T) is suppressed strongly at low temperature by magnetic eld, with MR \models ((T;H)-(T,0))/(T,0)] reaching 55% at 4 K and 14 T. The large negative M R com es from the reduction of spin scattering, which re ects a spin polarized transport. The reduction of spin scattering originates from the ferrom agnetic correlation, which can be deduced from the ferrim agnetic transition at about 19 K. The negative MR shown in g. 2 (b) increases with decreasing the tem perature, in contrast to the CMR in manganites¹⁵ or ReBaCo₂O₅₊ $r_{1}^{16,17}$ in which a maximum of MR can be observed around the phase transition tem perature. This indicates that the ferrom agnetic correlation in the conducting layers is rather weak or som e uctuation exists in the system . Figure 2 (b) shows a large negative MR below 20 K at 4 T, but no obvious M R above 20 K. This tem perature is alm ost the same as that of the ferrim aqnetic transition, re ecting the close relation between the spin polarized transport and the ferrom agnetic correlation inferred from ferrim agnetism. The MR displayed in

g. 2 (b) increases abruptly below a certain temperature at di erent elds (as indexed by the dashed arrow), and

this tem perature increases with enhancing external magnetic eld. Such a tem perature should correspond to the ferrim agnetic transition, which would be enhanced with increasing magnetic eld. These results support that the large negative M R arises from the ferrom agnetic correlation in conducting layers.

2. Magnetic-eld-induced IM transition

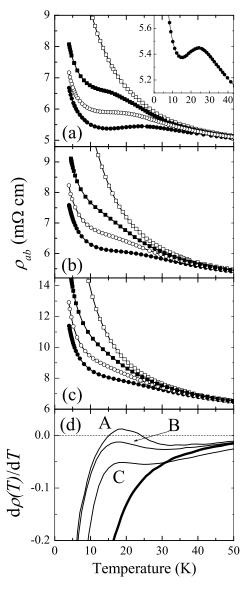


FIG. 3: Magnetoresistivity of the crystal A (a), B (b) and C (c) plotted against T in detail at magnetic elds of 0 T (), 7 T (), 10 T () and 14 T (), respectively. (d) The slope of (T) under the eld of 14 T for crystal A, B and C (solid lines) and of (T) without eld (bold line) for crystal A plotted against T. The inset shows the magni ed plot of 14 T data of crystal A in order to exhibit the IM transition clearly.

A most intriguing result in g. 2(a) is that a eldinduced weak insulator-to-m etaltransition at 14 T can be observed at about 25 K. The data below 50 K at 0, 7, 10, 14 T for crystalA, B, C are plotted in the g. 3(a), (b), and (c), respectively. In g. 3(a), there exhibits a clear downtum of (T) at about 25 K for 14 T data, at which the sign of slope d (T)/dT is changed from negative to positive, indicating that an insulator-m etal transition is induced by magnetic eld. Compared to the zero eld curve, (T) in magnetic elds lower than 14 T shows a notable change of the slope (d (T)/dT) at low tem perature. Fig. 3 (a) show sthat even (T) at 4 T begins to possess the marked change of the slope. It is similar to the cusp structure of (T) of B 1/2 x P bx Sr₂C o₂O y single crystals with x= 0.51. In $B_{\frac{1}{2}x} P b_x Sr_2 C o_2 O_y$ single crystals, the zero eld (T) shows an obvious downturn at 5 K for x = 0.51, which is thought to correspond to the ferrom agnetic transition.⁴ The cusp shifts to higher tem perature with increasing magnetic eld. This is also similar to the rapidly downturn of (T) around ferrom agnetic transition with decreasing T in the perovskite manganites¹⁵ and cobalt oxides¹⁸. These suggest that the $Ca_3Co_4O_9$ system is close to ferrom agnetic transition, especially in high magnetic eld, though a ferrom agnetic transition has not been found in this system experimentally yet. In the crystalA, ferrim agnetism instead of ferrom agnetism was observed in weak magnetic eld. No measurement has been performed in high eld. Nonetheless, inferred from the a notable change of the slope of (T) in m agnetic eld, our results seem to suggest that ferrin agnetism to ferrom agnetism transition possibly occurs when m agnetic

eld is enhanced.

For the crystalB and C with less oxygen content relative to the crystalA, no downtum behavior in (T) is observed even at 14 T, but it shows a rem arkable change in the slope d /dT at the ferrin agnetic transition tem perature (T_{FR}) , as shown in g. 3 (b) and 3 (c). In order to show clearly the above behavior, the slope d /dT vs. T curve presented in Fig. 3 (d). The d (T)/dT at zero eld varies m onotonically with tem perature, while d (T)/dT at 14 T for these three sam ples show a clear dip-hum p structure, which reveals a noticeable change of the slope of (T) around 10 K-30 K in m agnetic eld. The increase of the d (T)/dT toward to positive value with decreasing T indicates a downtum tendency of (T). O by jously, the tendency of the downtum of (T) decreases with reducing the oxygen content. A positive d /dT is clearly shown in g. 3(d) for the crystal A at 14 T, indicative of an insulator-metal transition. The eld-induced IM transition is ascribed to the enhancement of ferrom agnetic correlation. Thus the ferrom agnetic correlation is reduced with the loss of oxygen content. As shown in g. 1, SDW order is enhanced by the reduction of oxygen content. Thus the ferrom agnetic correlation seems to be $\operatorname{com} \operatorname{peting} w$ ith the SDW .

3. Magnetotransport in the as-grown crystal

C om pared to crystal A-D, the as-grown crystal E has a lower carrier concentration and thus a higher resistivity.

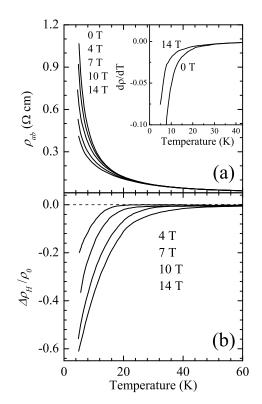


FIG. 4: (a) The temperature dependence of the transverse magnetoresistivity the in as-grown crystal. (b) Temperature dependence of the M R in various elds.

Figure 4 (a) show s the magnetoresistivity for the as-grow n crystalat various m agnetic elds. The large negative MR is also observed at low tem perature, like the crystal A -D.W hile no sign for a eld-driven IM transition can be found even at 14 T (see the inset of g. 4(a)). A reduction of carrier concentration in the as-grown crystal relative to the oxygen annealed ones could lead to an enhancement of SDW order as in the Bi-or Y-for-Ca substitution in $Ca_3Co_4O_{9+}$ sam ples.¹² In the literature, it is reported that the SDW transition temperature is increased by 30 K due to either Bior Y doping with x=0.3 in Ca_{3 x} M_xCo₄O₉ (M = Bi_yY). The T_{m in} for the as-grown crystal at zero eld is 149 K, which is much higher than that observed in the crystals annealed in oxygen ow. T_{m in} is associated to the SDW order.¹² Thus the increase of $T_{m in}$ is consistent with the enhancement of the SDW due to reduction of carrier concentration. In g. 4(b), the H = 0 shows negative value, indicative of a spin polarized transport like in crystal A. One can notice that in g. 4 (b) the tem perature for the H = 0beginning to show negative value enhances with increasing magnetic eld, suggesting a enhancem ent of ferromagnetic correlation with increasing magnetic eld as in crystal A. Nonetheless, the ferrom agnetic correlation is much weaker than that in the crystals annealed in oxygen so that no sign of downtum tendency of (T) can be found at 14 T in spite of the large negative MR.W hile a larger negative M R relative to crystal A is observed at

14 T in crystalE. The possible reason for this result will be discussed in the following.

4. The e ect of annealing condition on the transport behavior

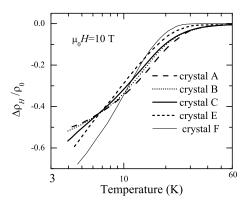


FIG.5: The magnetoresistance at 10 T as a function of T in the crystal A-C, E, and F.

A coording to the results above, the annealing condition a ects the transport and magnetotransport behaviors strongly. O byiously, the transport behavior is changed by varying oxygen content, i.e. by varying the Co ions valence. From crystal A to F, the evolution of resistivity indicates that the hole concentration is reduced due to the loss of oxygen content. The reduction of the Co ions valence due to the loss of oxygen content enhances the SDW order dram atically, which can be inferred from the large increase of the ${\tt T}_{\tt m\ in}$ as discussed above. Spin density wave is basically antiferrom agnetic, thus one can conclude that there is antiferrom agnetic correlation in the system and the loss of the oxygen favors the enhancem ent of the antiferrom agnetic correlation. Nonetheless, the ferrin agnetism and the large negative MR in the crystals suggest that there also exists ferrom agnetic correlation. Figure 5 exhibits the (H = 10T) / (H = 0T)vs. T for crystals A-C, E, and F, respectively. C learly, the tem perature below which the negative MR is observable increases with enhancing oxygen content. At very low tem perature, the absolute value of $_{\rm H} = _0$ increases with reducing the oxygen content. With increasing T, it gradually evolves to a completely opposite variation with oxygen content, that is, the absolute value of H = 0 decreases with reducting the oxygen content. This is very similar to the evolution of H = 0 with lead doping level in (Bi,Pb)₂Sr₂Co₂O_y system (Ref. 4, g. 9). With increasing Pb doping level, the tem perature below which negative MR is observable increases, and the value of MR is enhanced in the tem perature range from 8 to 40 K, while reduced below 8 K $\overset{4}{.}$ In (B i,Pb) $_2 \, {\rm Sr}_2 \, C \, o_2 \, O_{\, V}$, the increase of hole concentration due to Pb doping leads to a transition from param agnetism in Pb-free sample to weak ferrom agnetism in the sam ple with $Pb=0.51.^4$ Thus the

g. 5 suggests that the enhancement of oxygen content, i.e. the increase of C o ions valence, leads to the increase of the ferrom agnetic spin correlation. This is consistent with conclusion inferred from the evolution of the eldinduced IM transition by comparing the g. 3 and g. 4.

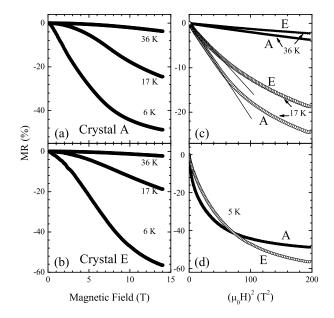


FIG.6: The isotherm alm agnetoresistance as a function of magnetic eld for crystalA (a) and E (b), respectively. The same data are replotted in (c) and (d) in the square magnetic eld scale.

The isotherm alMR shown in g. 6(a) and 6(b) further con ms this speculation. Fig. 6(a) and 6(b) shows the isotherm alMR for the crystalA and E, respectively. At 36 K and 17 K, the MR is larger in crystalA.W hile at 6 K, the MR in crystalA is smaller than that in crystal E below about 8.5 T, and with further increasing magnetic eld, the MR in crystal A becomes the smaller one (also see g. 6(d)). At 36 K and 17 K, the MR shows no saturation tendency, indicating that the spins is far from being completely polarized. The larger MR value in crystalA at 36 K and 17 K suggests a m ore polarized transport and thus a stronger ferrom agnetic correlation. At 6K, there is a clear saturation tendency of MR in high magnetic eld in both crystals. The larger MR in lower eld in crystal A indicates that the spin in this sample is easier to be polarized, since the magnetotransport is thought to be a spin polarized transport. The saturation of MR suggests a tendency of completely polarized spins. The smaller MR in crystalA at 6K in high magnetic eld suggests a less spin disordered transport. All of these strongly suggest a stronger ferrom agnetic correlation in crystalA and de nitely support the speculation that the enhancem ent of oxygen content leads to the increase of the ferrom agnetic spin correlation.

Fig. 6(a) and 6(b) is replotted in g. 6(c) and 6(d) in square magnetic eld scale. At 36 K, it is found that the

MR of the two crystals is proportional to H 2 . W hile the MR at 17 K is proportional to H 2 only in low magnetic

elds and deviates from H^2 law in high m agnetic elds. At the lower T, 6 K, it disobeys H^2 law from zero eld. These results suggest that there are probably di erent m echanisms for the negative M R at high T and low T. It should be pointed out that at 36 K there is (shortrange) IC-SDW order only, while 6 K is far below the ferrim agnetic transition, at which the the ferrim agnetism and (long-range) IC-SDW order coexist. consequently, the M R at 36 K only can re ect the property related to SDW state. W hile the M R at 6 K should m ostly reveal the e ect of ferrim agnetism . 17 K is just below the ferrim agnetic transition, thus the M R at this tem perature involves the in uence of these two m agnetism s.

5. The in uence of oxygen content and magnetic $% \mathcal{S}$ eld on the SDW order

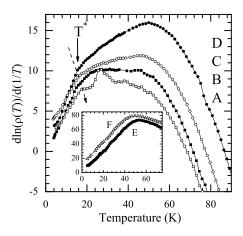


FIG.7: Logarithm ic derivatives of the zero- eld resistivity vs. T for crystalA, B, C, and D respectively. The inset shows the T dependence of the Logarithm ic derivatives of the zero- eld resistivity of crystalE.

W hy negative M R can be observed in IC-SDW state? In previous SDW materials, such as organic conductors (TM T SF)₂X (TM T SF: Tetrm ethltetraselena-fulvalene, $X = PF_6$, NO₃ and C D₄),^{19,20,21} were reported to show positive M R in SDW state. In order to investigate the nature of such negative M R, the e ect of a magnetic eld on the SDW order should be perform ed. U sually, in a SDW state, the resistivity (T) can be expressed as^{12,23}

$$\frac{1}{2} = (T) \exp \frac{g}{k_B T}$$
; (1)

where (T) is the mobility of carriers, $_{\rm g}$ is the gap energy, and $k_{\rm B}$ is the Boltzm ann constant. U sually, (T) is independent of T. U sing Eq. (1), the (T) of crystals A – D in T between 50 and 20–30 K can be tted by assuming that (T) is independent of T. In this case, dln /d (1=T) can be calculated to re ect the activation energy, $_{\rm g}$.²²

Fig. 7 shows the dln /d(1/T) plotted against T for all the crystals. Plateaus are observed in crystals A-D in the T ranging from 20-50 K. This reveals that in these sam ples there are T independent gap within this tem perature range, which could be opened by SDW . Fig. 7 exhibits that the value of the plateau of $d\ln = d(1/T)$ increases from crystal A to D. This is consistent with the evolution of $T_{m in}$ with the oxygen content, which re ects the SDW is enhanced by decreasing oxygen content. Thus it m ay suggest that the observed energy gap is opened by SDW \cdot^{23} According to SR and + SR results, \cdot^{12} it is considered that a short-range order IC -SDW state appears below 100 K, while the long-range order is com pleted below 30 K. In g. 7, dln /d (1/T) varies sm oothly through 30 K with decreasing tem perature, except for the crystal A. In crystal A, a sharp peak is observed around 27 K. The susceptibility and + SR experiment reveal that the long-range SDW order com pletes at this tem perature.¹² M oreover, the sharp peak of dln /d(1/T) was thought to correspond to the SDW transition temperature. 19,20,21 Thus, the peak of dln /d(1/T) in crystal A corresponds to the tem perature where long-range SDW order com pletes. Even so, the value of dln /d(1/T) is almost the same at the two sides of the peak. Fig. 7 indicates that the in uence of short-range and long-range IC -SDW order in this sam ple on the transport properties is the sam e.

The Eq. (1) cannot be applied in the whole range of T below 50 K because the dln /d(1/T) shows a rapidly decrease below a tem perature around 20 K, which is indexed as T in g. 7. According to the susceptibility experim ent,¹² a ferrim agnetic transition occurs around this tem perature. This suggests that the abrupt decrease of dln /d(1/T) below T arises from the ferrimagnetic transition. With increasing oxygen content from crystal D to crystal A, the T enhances slightly. The dln /d(1/T) re ects the activation gap. Thus, the abrupt drop of dln /d(1/T) suggests that the ferrin aqnetic transition reduces or hides the SDW gap. The inset shows the dln /d(1/T) of crystal E and F. In this two samples no plateau is observed, suggesting Eq. (1) is not feasible any more or the (T) is dependent on T in this two samples. There is no anomaly below 20 K, which could be due to the stronger SDW order and rather weaker ferrin agnetism in these two samples relative to the crystals annealed in oxygen atm osphere. The e ect of ferrim agnetism is hidden by the strong SDW order.

In order to study the in uence of magnetic eld on the SDW state, the dln /d(1/T) as a function of T at various magnetic eld in the two samples is shown in Fig. 8(a). It is observed that the value of the plateau decreases with increasing eld, indicating the reduction of the activation gap. W hile above 50 K, the dln /d(1/T) is almost independent of magnetic eld. As discussed above, the gap opening can be ascribed to the SDW order. If so, it suggests that the SDW order here is suppressed by magnetic eld. The peak around 27 K disappears when eld is as high as 7 T, suggesting that the SDW is suppressed indeed. This can be used to explain

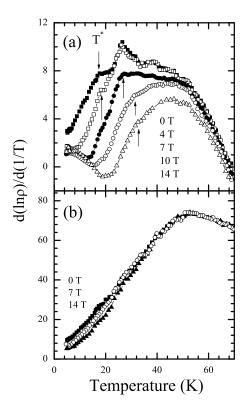


FIG. 8: (a) The logarithm ic derivative of the resistivity of crystal A as a function of the tem perature at 0, 4, 7, 10, and 14 T. (b) The tem perature dependence of The logarithm ic derivative of the resistivity of crystal E at 0, 7, 14 T.

the negative MR far above the ferrin agnetic transition tem perature, which has a di erent H dependence of the MR from that in ferrin agnetic state. Since the uptum resistivity below T_{m in} is associated with the SDW order, a suppression of SDW certainly leads to negative MR. In g. 8(a), T increases with increasing magnetic eld, while the slope of the dln /d(1/T) remains unchanged below T. The enhancement of the T is related to the increase of ferrin agnetic transition temperature in magnetic eld, consistent with the MR data in Fig. 2 (b). C learly, the ferrim agnetic ground state is competing with the SDW ground state. The suppression of SDW in high magnetic eld may be related to the enhancem ent of the ferrom agnetic correlation. A nother triangular layered cobaltite should be mentioned to compare with $[Ca_2CoO_3]_{0:62}$ $[CoO_2]$ is Na_xCoO_2 . In $Na_{0:75}CoO_2$, SDW and weakly ferrom agnetism coexist, 24,25,26 while

a large positive M R was observed in magnetic state,²⁷ contrasting to the negative M R in $[Ca_2CoO_3]_{0.62}$ [CoO₂]. The negative M R in $[Ca_2CoO_3]_{0.62}$ [CoO₂] originates from the reduction of the spin scattering of carriers, while in N $a_{0.75}CoO_2$, the M R seems to be more possible com - ing from the change of carrier-m obility in Ferm i surfaces in magnetic eld due to a pseudogap formation.²⁷ In spite of the weakly ferror agnetism, the pseudogap formation leads to a positive M R in the N $a_{0.75}CoO_2$. Finally, we note that the dln /d(1/T) vs. T curve in g.

8 (b) for crystal E remains unchanged above 20 K with varying magnetic eld, suggesting that the SDW is too strong to be suppressed by magnetic eld. Below 20 K, the dln /d(1/T) decreases with increasing magnetic eld, manifesting that there still is ferrim agnetic transition in crystal E in spite of the reduction of oxygen content with respect to the crystal A. This further demonstrates the point of veiw that the ferrom agnetic correlation leads to the large negative MR.

C. Therm al-activation transport in magnetic eld at low temperature

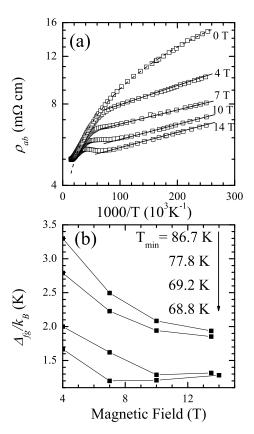


FIG.9: (a) A mhenius plot for the data of g. 1(a). The dashed line is the tting data with M ott variable range hopping law. The solid line is the t data with the therm al activation form alism. (b) The eld-induced energy gap ($_{\rm fg}$) plotted against magnetic eld for four crystals with di erent T_{m in}.

In Fig. 8(a) another intriguing feature can be found in the low temperature range, the dln /d(l=T) shows a T-independent behavior below about 10 K for the data in magnetic eld. It suggests that there is another therm alactivation transport. The A mhenius plot of the data in g. 1(a) is displayed in g. 9(a), which clearly shows that the temperature dependence of the resistivity under di erent elds exhibits an A mhenius-type behavior below about 12 K, that is, (T) / $e^{-k_B T}$, where is gap energy and k_B is Boltzm ann constant. It suggests that the resistivity in low temperature range under the elds follows the therm al activation model. While the zero

eld data below 30 K can be well tted by a formula (T) = $A e^{(T_0 = T)^{1=4}}$, indicative of M ott variable range hopping (VRH) law. It im plies that an energy gap is opened by magnetic eld. It should be pointed out that this phenom enon was observed in all of the four oxygen annealed crystals A-D, with di erent Tmin. The obtained gap energy depends on $T_{m in}$. Figure 9(b) shows the magnetic dependence of the eld-induced gap energy for the four crystals. It is found that the gap energy increases with increasing T_{m in}. W hile it decreases with increasing magnetic elds, and saturates in high eld. It should be pointed out that no such phenom enon is observed in the as-grown crystal and the sample annealed in N_2 . The nature of this eld-induced therm all activation transport is not well understood yet. The gap energy shown in g. 9(b) is dependent on $T_{m in}$, suggesting that the gap may be associated with the SDW order.

IV. D ISCUSSION

Large negative ΜR has bæn observed many mist-layered in cobaltites, such as: $[S \, r_{1\,:9} P \, b_{0\,:7} C \, o_{0\,:4} O_{\,3} \,] [C \, oO_{\,2} \,]_{1\,:8}$, $(B i; P b)_2 S r_2 C o_2 O_v,$ [B i_{1:7}C o_{0:3}C a₂O₄][C oO₂]_{1:67}, and $[Ca_2CoO_3]_{0:62}$ $[CoO_2]$ studied in this paper. In some of these cobaltites, such as [Sr1:9Pb0:7C 00:403][C 002]1:8 and $[Bi_{1:7}Co_{0:3}Ca_{2}O_{4}][CoO_{2}]_{1:67}$ spin density wave was observed.²⁵ W hile in some others, like (Bi,Pb)_2Sr_2Co_2O_y, ferrom agnetic transition was observed. In $[Ca_2CoO_3]_{0:62}$ $[CoO_2]$ single crystals, spin density wave and ferrin agnetic transition were observed by + SR and susceptibility experiments, 12 respectively.

N a_x C OO_2 is the most extensively studied at experimental and theoretical level in the layered cobaltites with triangular [C OO_2] layers as basic structure units. Because of the very similar structure of [C OO_2] layers, most of the results obtained in N a_x C OO_2 can be reproduced in the m is t cobaltites. The low-spin state of C d^+ and C d^{++} predicted by Singh in N a_x C OO_2 , ²⁸ is found to hold in (B i,P b)₂Sr₂C o_2O_y by photoem ission experiment.³⁰ A n-other prediction by Singh in N a_x C OO_2 , that the t_{2g} orbits are split into a_{1g} and e_g^0 subbands due to rhom bohedral crystal edt_r^{28} is feasible in (B i,P b)₂Sr₂C o_2O_y . O bviously, some theoretical results obtained in N a_x C OO_2 can be used in the m is t cobaltites.

A very important prediction from local spin density approximation (LSDA) band calculation by Singh is the ferrom agnetic instability in $Na_x CoO_2$.^{28,29} W hile experimentally, ferrom agnetism has not been observed. Only weakly ferrom agnetism ^{24,25,26} or m etam agnetism ³¹ was observed, which is probably due to quantum

uctuation^{24,28,29} N eutron inelastic scattering gives evidences for the existence of ferrom agnetic (FM) spin uctuation within the $[COO_2]$ layers in $Na_{0:75}COO_2$ single crystal.²⁴ The weak ferrom agnetism in $Na_{0:75}COO_2$ was thought to originate from a canted-SDW ^{25,26} or a spin

arrangem ent with an in-plane ferrom agnetic order and a SDW modulation perpendicular to the planes.²⁴ M etamagnetism in $Na_{0:85}CoO_2$ was suggested to favor the in-plane ferrom agnetic correlation and interplane antiferrom agnetic (AF) coupling.³¹ The M etam agnetism was thought to be a spin- op transition from an AF to a FM state along c-axis.³¹ The ferrom agnetic spin correlation is very sensitive to the Co ions valence in the triangular cobaltites. In $(BiPb)_2 Sr_2 Co_2 O_v$,⁴ with increasing Pb doping level from zero to 0.51, it can change from param agnetism to weak ferrom agnetism . Though no ferrom agnetism is observed in [Ca2CoO3]0:62 [CoO2], it shows sim ilarM R behavior to $(B_1, P_b)_2 Sr_2 Co_2 O_v$, especially the variation of the MR with oxygen content in g.5 is very similar to the evolution of MR with Pb doping level in $(B_1P_b)_2 Sr_2 C_0 O_y$. In the $[C_2 C_2 O_3]_{0:62} [C_0 O_2]$ crystals, a ferrin agnetism was found below 19K in susceptibility experiment, suggesting the ferrom agnetic correlation in conducting $C \circ O_2$ layers safely. The evolution of MR with oxygen content and the eld-induced downtum of (I) indicate that the ferrom agnetic correlation varies dram atically with Co ions valence. Especially, the eldinduced IM transition in crystalA occurs at the ferrin agnetic transition. This is similar to the insulator-metal transition induced by eld at the ferrom agnetic transition in $(BiPb)_2Sr_2Co_2O_v$ with Pb=0.51.⁴ The Na_{0:75}CoO₂, which possesses weak ferrom agnetism, 24,25,26,27,31 exhibits large positive instead of negative MR observed in $(BiPb)_2 Sr_2 Co_2 O_v$. This was considered to be due to a pseudogap form ation deduced from the abrupt downtum of resistivity.27

A nother interesting magnetic property in this system is spin density wave. The SDW emerges from much higher temperature than ferrim agnetism 12 A coording to our data, the negative M R appears far below $T_{\rm m\ in}$, and it coincides with the ferrim agnetic transition. In contrast to ferrom agnetic correlation, the SDW has a complete opposite response to C o ion valence. The SDW enhances with reducing C o ion valence according to the change of $T_{\rm m\ in}$. This indicates that the ferrim agnetism and the SDW order are competing.

It is worthy of note that the SDW and ferrom agnetic correlation a ect the transport and magnetotransport properties strongly, suggesting that the SDW and ferrom agnetic correlation coexist in the $[CoO_2]$ conducting sheets below ferrin agnetic transition temperature. The + SR experiments have suggested the coexistence of the IC-SDW state and ferrin agnetism below 19 K.¹² Sugiyam a et al. suggested that the two subsystem softhe crystal structure (the $[Ca_2CoO_3]$ rocksalt-type layers and the $[C \circ O_2]$ triangular sheets) act directly as the two m agnetic sublattices for the ferrim agnetism \cdot^{12} From this picture, one can naturally infer the existence of ferromagnetic spin arrangement in the $[C \circ O_2]$ sheets. Large negative MR and the eld-induced IM transition seems to support this picture for the ferrom agnetic correlation in the conducting [CoO₂] sheets. However, we cannot give detailed picture how the spin arrangement for the

coexistence of ferrim agnetism and the (long-range order) IC-SDW below T_{FR} because of the absence of the microscopic information of the spins in Co ions. Nonetheless, in $[Ca_2CoO_3]_{0:62}$ $[CoO_2]$, it cannot be a canted-SDW as that found in $Na_{0.75}CoO_2^{25,26}$ because the spin moments of both SDW and ferrin agnetism are along c-axis and cannot be detected in the $[\cos 2]$ planes according to ⁺ SR and susceptibility experiment. Also it is very di cult to expect the $[Ca_2CoO_3]_{0:62}[CoO_2]$ with inplane ferroam gnetic order and a SDW modulation perpendicular to the planes as proposed by another authors in Na_{0:75}CoO₂²⁴ because of the m is t structure between $[Ca_2CoO_3]$ and $[CoO_2]$ subsystem s. Another possible picture is that the SDW order is ferrom agnetic, while the SDW order is basically antiferrom agnetic. Thus, a macroscopic magnetism should be ferrim agnetic, as actually observed below 19 K.Co-NMR and neutronscattering experim ents are desired to m ake out the exact m agnetic structure of $[Ca_2CoO_3]_{0:62}$ $[CoO_2]$.

V. CONCLUSION

To sum m arize, the in-plane resistivity was measured in $[Ca_2CoO_3]_{0:62}$ $[CoO_2]$ single crystals in magnetic elds up to 14 T. The zero eld _{ab} (T) exhibits a minimum and

 $T_{m\ in}$ increases with decreasing the oxygen content, indicative of the enhancement of SDW. The SDW strongly depends on the carrier concentration or oxygen content. Large negative MR is observed for all crystals. While a

eld-induced IM transition in high magnetic eld were observed only in the crystal annealed in oxygen atmosphere. These results suggests there is ferrom agnetic correlation in the system and the correlation is enhanced by increasing oxygen content and magnetic eld. The strong e ect of oxygen content on the transport and magnetotransport behavior in plies that both the SDW and ferrim agnetism locate within the conducting $[CoO_2]$ sheets.

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E lectronic address: chenxh@ ustc.edu.cn

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